

850nm 25W Pulsed VCSEL Diode in 2016 Package

Part No. VC20A-850H25WA (Substrate AlN) | VC20C-850H25WA (Substrate CuAg)

Features

- 2016 package
- Good thermal conduction
- Short rise time
- Oxide isolation technology
- High reliability and Easy to collimate
- 25W 850nm VCSEL @ 81A, pulse width 8.8ns



Substrate AlN, Package 2016

Applications

- Proximity sensor
- Laser curtain
- 3D sensor
- Range finder sensor
- 3D detection
- Scanning lidar



Substrate CuAg, Package 2016

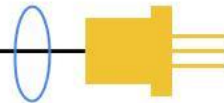
Specifications

Absolute Maximum Ratings				
Parameters	Symbol	Rating	Unit	Conditions
Case Operating Temperature	Top	-40 to 85	°C	
Storage Temperature	Tstg	-40 to 105	°C	
Reflow Soldering Temperature	Tsol	260°C	°C	10 seconds
Reverse Voltage	Vr	5	V	
Maximum Continuous Current	Imax	90	A	Duty cycle 0.1% max
ESD Exposure (Human Body) Model	ESD	2K	V	

Notes:

- Stresses greater than those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or other conditions above those indicated in the operations section for expanded periods of time may affect reliability.
- In its maximum rating diode laser operation could damage its performance or cause potential safety hazard such as equipment failure.
- Electrostatic discharge is the main reason for laser fault of the diode. Take effective precautions against ESD. When dealing with laser diodes, use wrist strap, grounding work surface and strict antistatic technology.

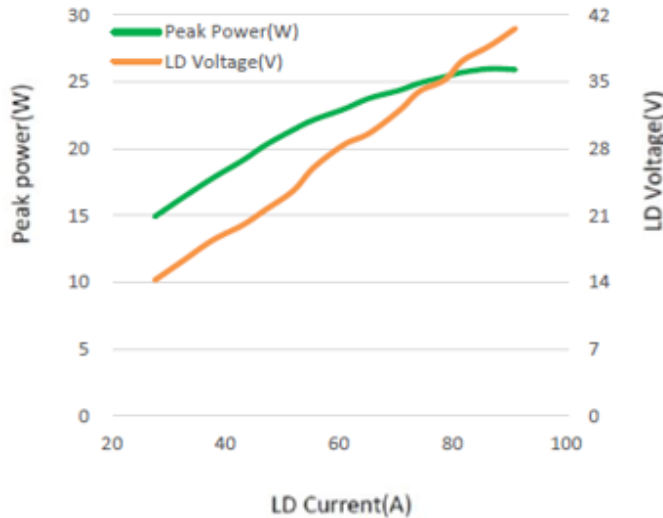
Electro-Optical Characteristics (T _{op} =25°C, Pulse width 8.8ns at 11.68 kHz)						
Parameters	Symbol	Min.	Typ.	Max.	Unit	Conditions
Optical Output Power	P _o	20	25	30	W	I _F =81A
Threshold Current	I _{th}	-	0.1	-	A	
Forward Pulse Current		-	81	-	A	
Emission Area		-	370 x 371	-	um	
Peak Wavelength	λ _P	840	850	860	nm	P _o =25W
Pulse Forward Voltage	V _F	36	37	38	V	I _F =81A
Series Resistance	R _S	0.44	0.46	0.47	Ohm	I _F =81A
Beam Angle	Θ	-	20	-	Deg	I _F =81A
Wavelength Temperature Drift	Δλ _p / ΔT	-	0.07	-	nm/°C	I _F =81A
Rise Time	Tr	-	2.8	-	ns	
Soldering Temperature	Tsol			260	°C	10 seconds
Duty Cycle		-	-	0.1	%	
Substrate						AlN; CuAg



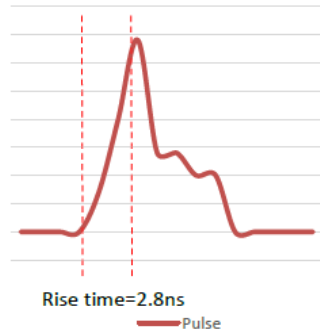
Environmental Specifications						
Parameters	Symbol	Min.	Typ.	Max.	Unit	Conditions
Case Operating Temperature	Top	-40	20	85	°C	
Storage Temperature	Tstg	-40	20	105	°C	

Typical Characteristics

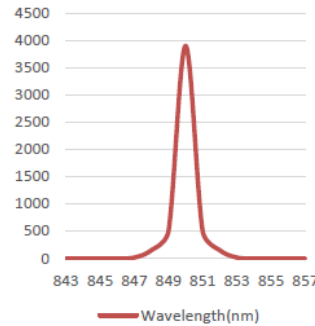
LIV Graph



Pulse width=8.8ns

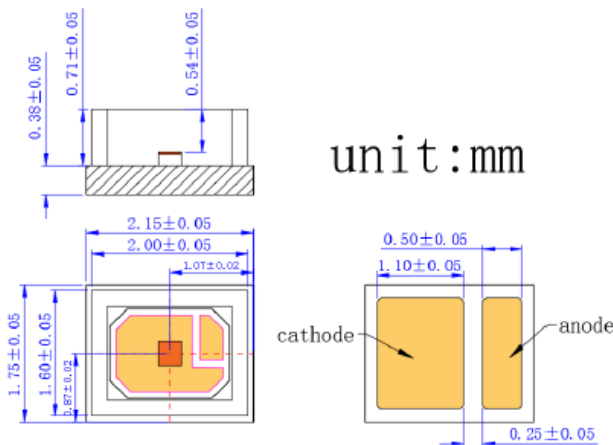


Intensity vs. Wavelength

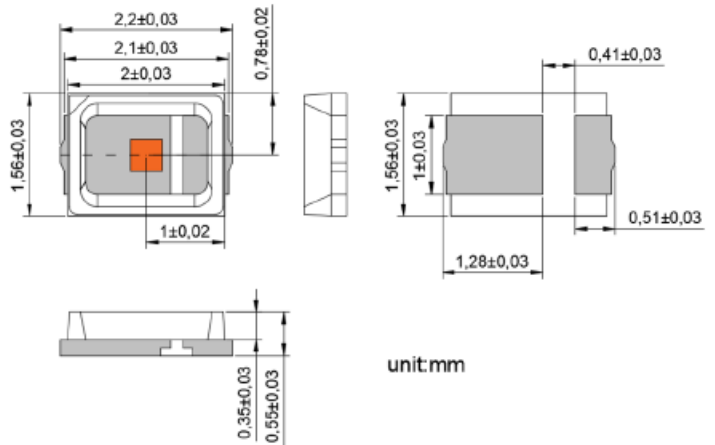


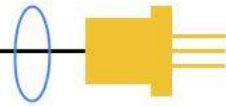
Outline Dimensions (unit: mm)

Substrate AlN, Package 2016

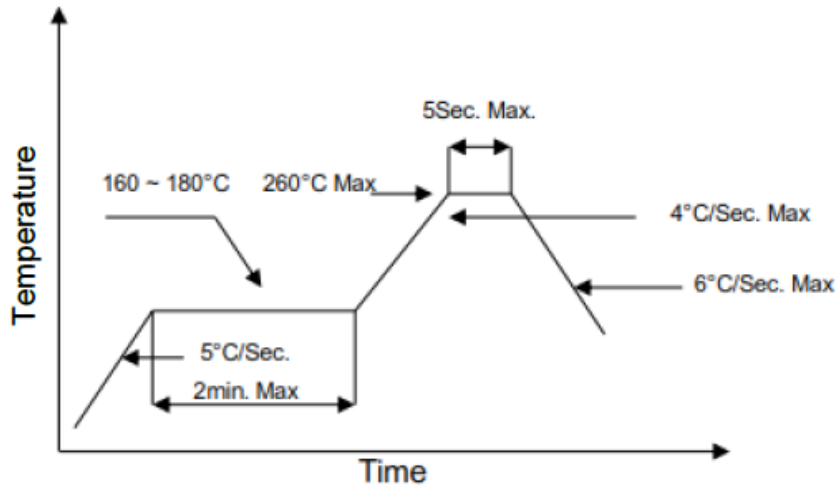


Substrate CuAg, Package 2016





SMT Reflow Soldering Curve



Note: Reflow soldering can be operated only one time. During the temperature ramp-up, no forces may be exerted on the LD which would deform or damage them. After soldering is completed, please do not process until the product temperature ramps down to room temperature.

Additional Notes

1. Please use solder paste to cure the laser diode.
2. Please make sure that the heat of VCSEL diode has been completely conducted to metal shell to avoid affecting the optical power output.
3. This VCSEL diode can be only used in constant voltage and current.
4. Please do not aim the laser at people or animals.
5. You may observe the laser spot through an image monitoring equipment.
6. Please do not touch VCSEL diode surface by naked hands or squeeze the sealant on VCSEL diode surface. It may cause wrong optical angle and distorted laser spot, and even damage the VCSEL diode.
7. Please use ceramic suction nozzle to absorb the VCSEL diode, so as to avoid VCSEL diode sticking to the nozzle.
8. Please add a 0.02s blowing action after locating the laser diode to aluminum substrate.
9. Specifications are subject to change without notice.